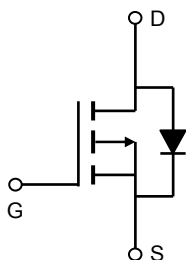
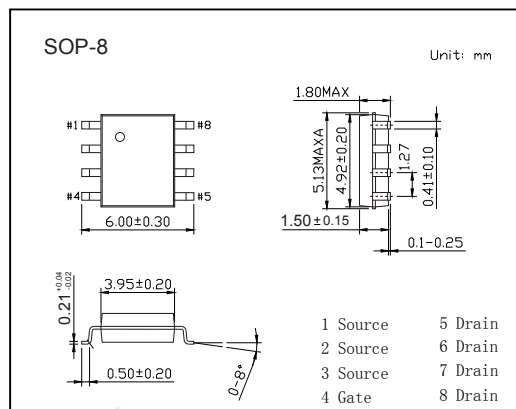


P-Channel MOSFET

AO4435 (KO4435)

■ Features

- $V_{DS}(V) \approx -30V$
- $I_D \approx -10.5 A$ ($V_{GS} \approx -20V$)
- $R_{DS(ON)} < 14m\Omega$ ($V_{GS} \approx -20V$)
- $R_{DS(ON)} < 18m\Omega$ ($V_{GS} \approx -10V$)
- $R_{DS(ON)} < 36m\Omega$ ($V_{GS} \approx -5V$)

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	± 25	
Continuous Drain Current	$T_A = 25^\circ C$	I_D	-10.5	A
	$T_A = 70^\circ C$		-8	
Pulsed Drain Current		I_{DM}	-80	
Avalanche Current		I_{AR}	-20	
Repetitive Avalanche Energy	$L = 0.3mH$	E_{AR}	60	mJ
Power Dissipation	$T_A = 25^\circ C$	P_D	3.1	W
	$T_A = 70^\circ C$		2	
Thermal Resistance.Junction- to-Ambient	$t \leq 10s$	R_{thJA}	40	$^\circ C/W$
	Steady-State		75	
Thermal Resistance.Junction- to-Lead		R_{thJL}	24	
Junction Temperature		T_J	150	$^\circ C$
Junction Storage Temperature Range		T_{stg}	-55 to 150	

P-Channel MOSFET

AO4435 (KO4435)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =-250 μA, V _{GS} =0V	-30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V			-1	μA
		V _{DS} =-30V, V _{GS} =0V, T _J =55°C			-5	
Gate-Body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±25V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} I _D =-250 μA	-1.7		-3	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =-20V, I _D =-11A			14	mΩ
		V _{GS} =-20V, I _D =-11A T _J =125°C			19	
		V _{GS} =-10V, I _D =-10A			18	
		V _{GS} =-5V, I _D =-5A			36	
On state drain current	I _{D(ON)}	V _{GS} =-10V, V _{DS} =-5V	-80			A
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-10A		22		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =-15V, f=1MHz		1130	1400	pF
Output Capacitance	C _{oss}			240		
Reverse Transfer Capacitance	C _{rss}			155		
Gate resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz	1		8	Ω
Total Gate Charge (10V)	Q _g	V _{GS} =-10V, V _{DS} =-15V, I _D =-10A		18	24	nC
Total Gate Charge (4.5V)				9.5		
Gate Source Charge	Q _{gs}			5.5		
Gate Drain Charge	Q _{gd}			3.3		
Turn-On DelayTime	t _{d(on)}			8.7		
Turn-On Rise Time	t _r	V _{GS} =-10V, V _{DS} =-15V, R _L =1.5Ω, R _{GEN} =3Ω		8.5		ns
Turn-Off DelayTime	t _{d(off)}			18		
Turn-Off Fall Time	t _f			7		
Body Diode Reverse Recovery Time	t _{rr}	I _F =-10A, dI/dt=100A/us		25	30	nC
Body Diode Reverse Recovery Charge	Q _{rr}			12		
Maximum Body-Diode Continuous Current	I _S				-3.5	A
Diode Forward Voltage	V _{SD}	I _S =-1A, V _{GS} =0V			-1	V

Note : The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

■ Marking

Marking	4435 KC****
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P-Channel MOSFET

AO4435 (KO4435)

■ Typical Characteristics

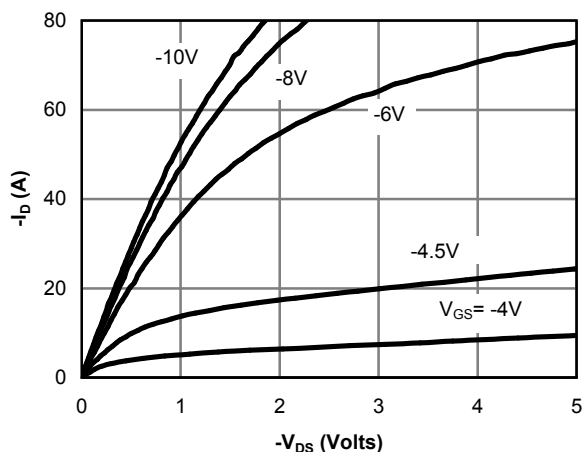


Figure 1: On-Region Characteristics

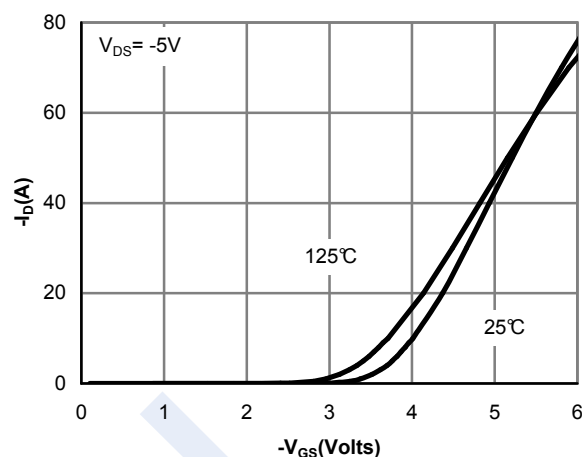


Figure 2: Transfer Characteristics

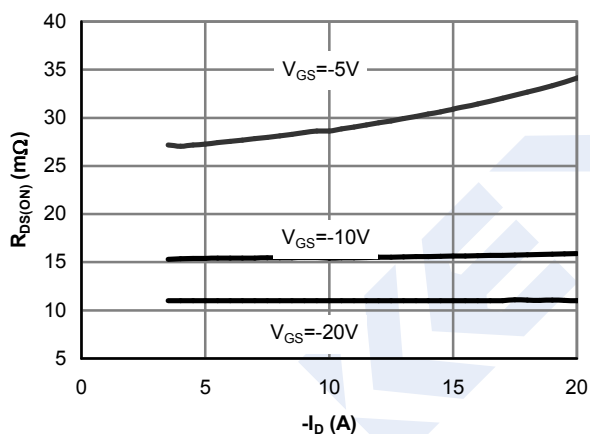


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

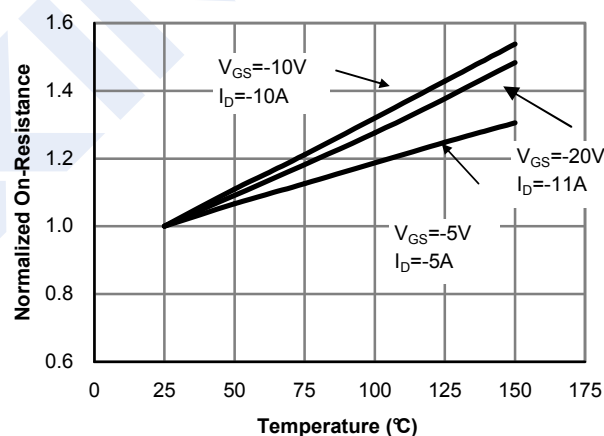


Figure 4: On-Resistance vs. Junction Temperature

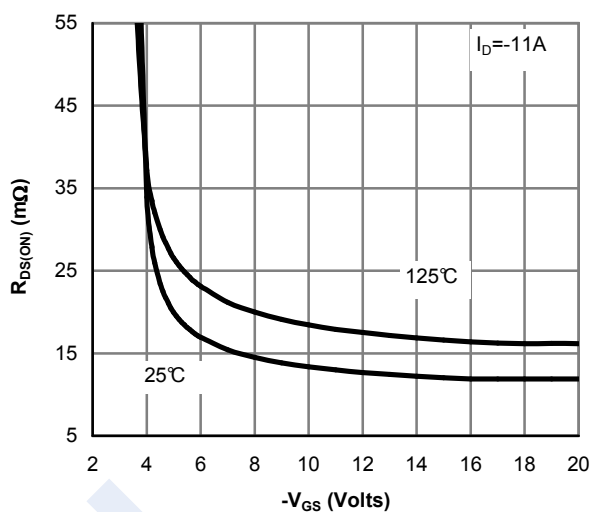


Figure 5: On-Resistance vs. Gate-Source Voltage

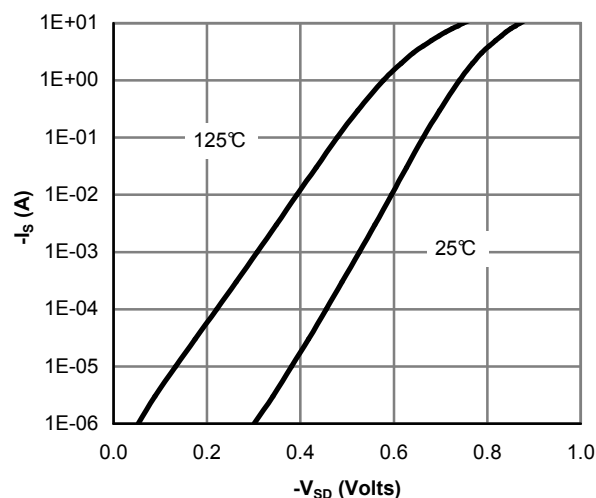


Figure 6: Body-Diode Characteristics

P-Channel MOSFET

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■ Typical Characteristics

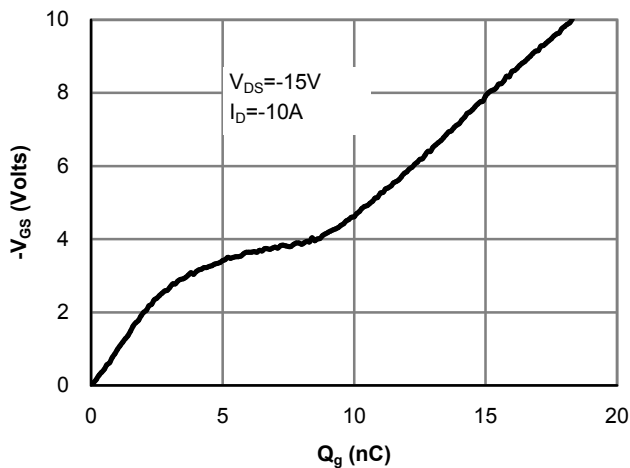


Figure 7: Gate-Charge Characteristics

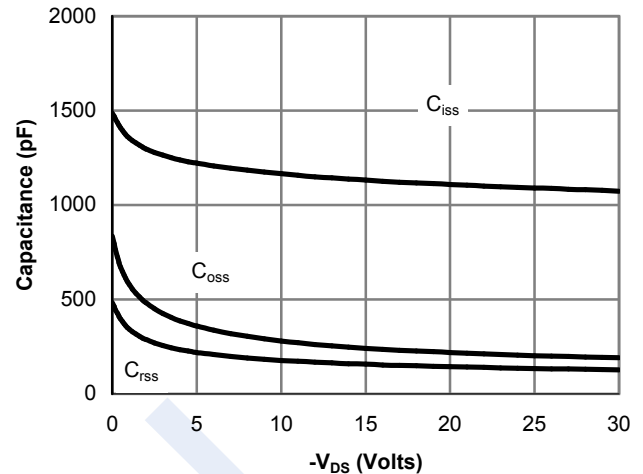


Figure 8: Capacitance Characteristics

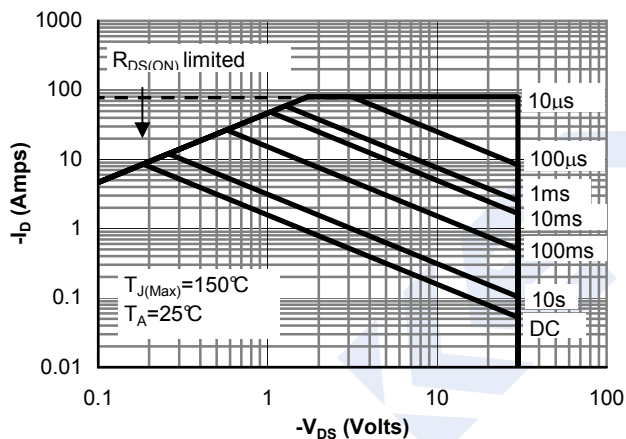


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

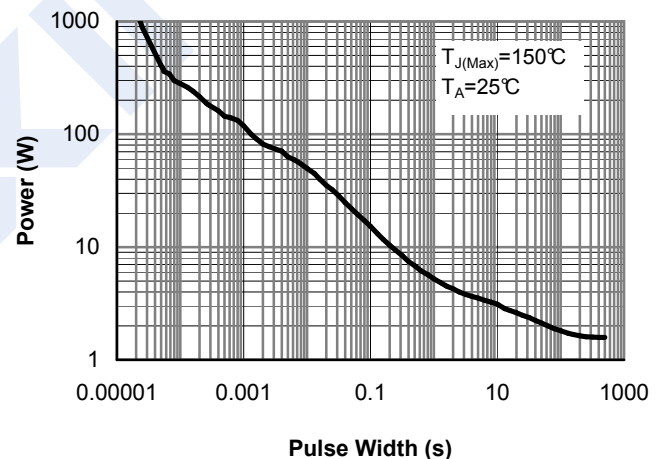


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

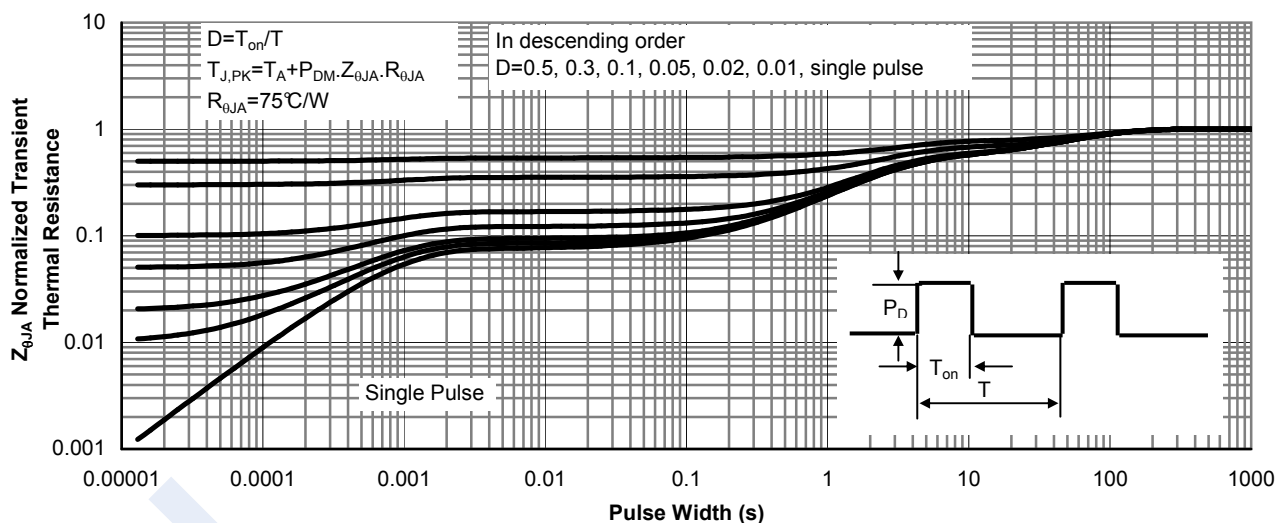


Figure 11: Normalized Maximum Transient Thermal Impedance(Note E)